



**HAL**  
open science

## Hole mobility in Ge/Si core/shell nanowires: What could be the optimum?

Jing Li, Narjes Jomaa, Yann-Michel Niquet, Moncef Said, Christophe Delerue

► **To cite this version:**

Jing Li, Narjes Jomaa, Yann-Michel Niquet, Moncef Said, Christophe Delerue. Hole mobility in Ge/Si core/shell nanowires: What could be the optimum?. *Applied Physics Letters*, 2014, 105 (23), pp.233104. <10.1063/1.4903475>. <hal-02137824>

**HAL Id: hal-02137824**

**<https://hal.science/hal-02137824v1>**

Submitted on 27 May 2022

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire HAL, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.




HAL Authorization

# Hole mobility in Ge/Si core/shell nanowires: What could be the optimum?

Cite as: Appl. Phys. Lett. **105**, 233104 (2014); <https://doi.org/10.1063/1.4903475>

Submitted: 29 October 2014 • Accepted: 22 November 2014 • Published Online: 08 December 2014

 Jing Li, Narjes Jomaa, Yann-Michel Niquet, et al.



View Online



Export Citation



CrossMark

## ARTICLES YOU MAY BE INTERESTED IN

[Electronic structure and electron mobility in  \$\text{Si}\_{1-x}\text{Ge}\_x\$  nanowires](#)

Applied Physics Letters **110**, 052102 (2017); <https://doi.org/10.1063/1.4975066>

[Carrier mobility in strained Ge nanowires](#)

Journal of Applied Physics **112**, 084301 (2012); <https://doi.org/10.1063/1.4759346>

[Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys](#)

Journal of Applied Physics **80**, 2234 (1996); <https://doi.org/10.1063/1.363052>

Lock-in Amplifiers  
up to 600 MHz



Zurich  
Instruments



## Hole mobility in Ge/Si core/shell nanowires: What could be the optimum?

Jing Li,<sup>1</sup> Narjes Jomaa,<sup>2</sup> Yann-Michel Niquet,<sup>1</sup> Moncef Said,<sup>2</sup> and Christophe Delerue<sup>3,a)</sup>

<sup>1</sup>Univ. Grenoble Alpes, INAC-SP2M, L\_Sim, Grenoble, France and CEA, INAC-SP2M, L\_Sim, Grenoble, France

<sup>2</sup>Laboratoire de la Matière Condensée et de Nanosciences, Faculté des Sciences, Université de Monastir, Monastir, Tunisia

<sup>3</sup>IEMN - Department ISEN, UMR CNRS 8520, Lille, France

(Received 29 October 2014; accepted 22 November 2014; published online 8 December 2014)

Recent experimental works have shown that Ge/Si core/shell nanowires (NWs) are very attractive for nanoelectronics and for low-temperature quantum devices, thanks to the confinement of holes in the Ge core. Reported hole mobilities of the order of  $200 \text{ cm}^2/\text{V/s}$  are promising for high-performance field-effect transistors. However, we demonstrate that mobilities more than ten times higher, up to  $8000 \text{ cm}^2/\text{V/s}$ , could be reached in Ge/Si NWs. Atomistic calculations reveal the considerable influence of the strains induced by the Si shell on the hole transport, whatever the NW orientation. The enhancement of electron-phonon interactions by confinement, which usually degrades the mobility in NWs, is therefore outbalanced by the effect of strains. © 2014 AIP Publishing LLC.

[<http://dx.doi.org/10.1063/1.4903475>]

Semiconductor nanowires (NWs) have attracted considerable attention not only for fundamental studies on one-dimensional (1D) structures but also as building blocks for nano-devices.<sup>1,2</sup> Among them, Ge/Si core/shell NWs with a radial heterostructure are particularly attractive.<sup>3–7</sup> The valence band offset between the Ge core and the Si shell indeed confines the holes in the core, where they form a 1D gas.<sup>3</sup> Ge/Si NWs are serious candidates for high-performance field-effect transistors (FETs), since the Si shell reduces scattering of holes by the NW surface.<sup>4–6,8,9</sup> As a matter of fact, recent experimental studies confirm that the presence of a Si shell strongly enhances the mobility of holes in Ge NWs, by a factor up to ten.<sup>6,9</sup> The measured mobilities in Ge/Si NWs can be of the order of  $700 \text{ cm}^2/\text{V/s}$ ,<sup>4</sup> and a recent comprehensive study reported a constant mobility of  $200 \text{ cm}^2/\text{V/s}$  in 15–30 nm diameter Ge cores with a 3 nm Si shell.<sup>9</sup> Even if the mobilities extracted from measurements on Ge/Si NW FETs are somehow scattered,<sup>4–6,8–10</sup> they are consistently within the same order of magnitude, i.e., hundreds of  $\text{cm}^2/\text{V/s}$ , which can be exploited in high-performance devices<sup>4,11</sup> and low-temperature quantum devices.<sup>3,10</sup>

In spite of these very promising results, the measured hole mobility remains much smaller in Ge/Si NWs than in bulk Ge ( $1900 \text{ cm}^2/\text{V/s}$ ).<sup>12</sup> It is not clear whether this important reduction is intrinsic (electron-phonon coupling) or extrinsic (e.g., interface roughness or impurity scattering). It is well known that the electron-phonon coupling in NWs is strongly enhanced by confinement, but this can be compensated by a decrease of the hole effective masses.<sup>13–16</sup> In addition, the presence of a Si shell induces radial compressive strains on the Ge core that shall increase the hole mobility in Ge NWs,<sup>17,18</sup> as already known in bulk Ge.<sup>19</sup> In order to assess the performances of present and future devices, it is therefore essential to understand how large the intrinsic mobility can be in perfect Ge/Si NWs.

In this context, we present atomistic calculations of the low-field phonon-limited mobility in Ge/Si core/shell NWs taking into account the effects of quantum confinement and strains on the electron and phonon band structures, and on the electron-phonon coupling. We show that the strains imposed by the Si shell considerably enhance the hole mobility in Ge/Si NWs with respect to pure Ge NWs and even bulk Ge, whatever the NW orientation. For NWs with 10 nm diameter cores and 1 nm thick shells, we predict mobilities ranging from 3 000 to 10 000  $\text{cm}^2/\text{V/s}$ , and mean-free-paths above 100 nm at 300 K. Although the hole mobility decreases at high carrier density, it remains much larger than the reported experimental data, which suggests that extrinsic scattering processes still limit the mobility in spite of the hole confinement by the Si shell. In addition, we cannot exclude that the experimental protocols based on NW FETs underestimate the mobilities,<sup>9</sup> which would be consistent with the quasi-ballistic transport and the mean-free-paths above 100 nm reported at room temperature.<sup>3,20</sup>

The electron band structure of the NWs is computed with the  $sp^3d^5s^*$  tight-binding model of Ref. 21, which reproduces all effective masses and deformation potentials of bulk Si and Ge. Spin-orbit coupling is taken into account. We calculate the phonon-limited mobility within a fully atomistic framework.<sup>13,16</sup> For that purpose, we compute the phonon band structures using a Valence Force Field model.<sup>22</sup> The electron-phonon interactions are obtained from the derivatives of the tight-binding Hamiltonian with respect to the atomic positions. All scattering processes fulfilling energy and momentum conservation are considered. Boltzmann's transport equation is solved exactly for the low-field mobility. Details on the methodology are given in Refs. 13 and 16. Unless specified, the mobility is calculated at low carrier density ( $E_f - E_v \gg kT$ , where  $E_f$  is the Fermi energy and  $E_v$  is the top of the valence band). Using exactly the same methodology, the hole mobility in bulk Ge is  $2280 \text{ cm}^2/\text{V/s}$ , 20% larger than the experimental value ( $1900 \text{ cm}^2/\text{V/s}$ )<sup>12</sup> usually

<sup>a)</sup>Electronic mail: christophe.delerue@isen.fr

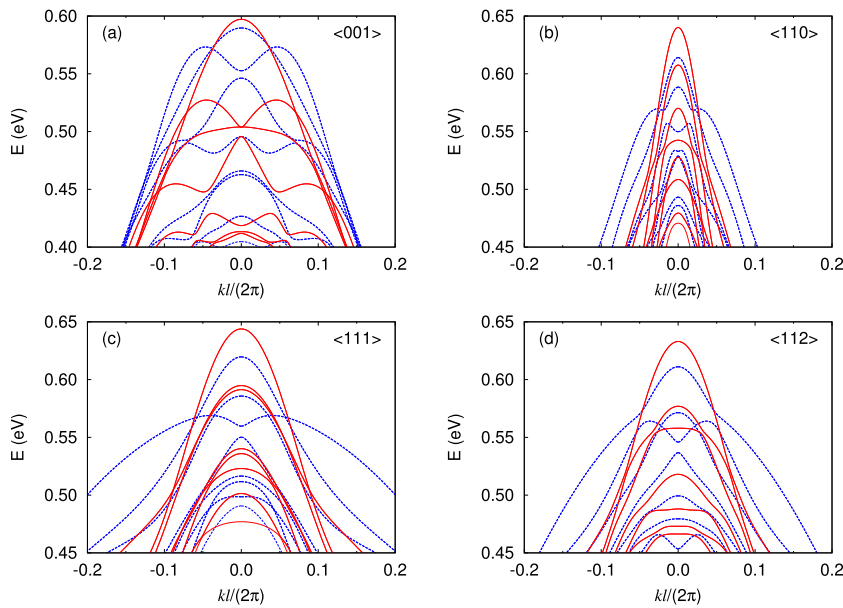


FIG. 1. Valence band structures of NWs with  $\langle 001 \rangle$  (a),  $\langle 110 \rangle$  (b),  $\langle 111 \rangle$  (c), and  $\langle 112 \rangle$  (d) orientations. Blue dashed lines: pure Ge NWs (diameter = 6 nm); red solid lines: Ge/Si core/shell NWs (core diameter = 6 nm, shell thickness = 1 nm).  $l$  is the length of the NW unit cell.

taken as reference (higher values were reported, such as  $2060 \text{ cm}^2/\text{V/s}$  in Ref. 23).

Hereafter, the NWs will be characterized by their core diameter  $d$  and their shell thickness  $t$ . In order to account for the 4.2% lattice mismatch between Ge and Si, the atomic structure of the NWs is relaxed with the same Valence Force Field model as for phonons. The elastic energy is expanded in power series of variables  $\tilde{h}_{ii} = u_i^2 - 3$  and  $\tilde{h}_{ij} = \mathbf{u}_i \cdot \mathbf{u}_j + u_i^2/6 + u_j^2/6$ .<sup>13,22,24</sup> Here,  $i$  labels the bonds of vector  $\mathbf{x}_i$  joining two neighbor atoms,  $\mathbf{u}_i$  being equal to  $4\mathbf{x}_i/a_i$ , where  $a_i$  is the lattice parameter.  $\tilde{h}_{ii}$  and  $\tilde{h}_{ij}$  measure bond stretching and bond-angle bending, respectively, ( $i$  and  $j$  share a same atom).<sup>24</sup> Only second order terms are considered in the power expansion as it was already demonstrated that higher-order terms have a negligible effect on structural and transport properties of Si NWs under strains up to several percent.<sup>25</sup> The coefficients of expansion are taken from Ref. 22 for Si and Ge, and average coefficients are used for Si-Ge bonds, following an approximation that works remarkably for  $\text{Si}_x\text{Ge}_{1-x}$  alloys.<sup>21</sup> In agreement with linear elasticity theory,<sup>26</sup> we have found that the resulting strains parallel ( $\varepsilon_{\parallel}$ ) and perpendicular ( $\varepsilon_{\perp}$ ) to the NWs are fairly homogeneous in the Ge core. For example,  $\varepsilon_{\parallel} \approx -1.22\%$  and  $\varepsilon_{\perp} \approx -0.2\%$  for a  $\langle 001 \rangle$  NW with  $d = 10 \text{ nm}$  and  $t = 1 \text{ nm}$ .

Figure 1 shows the hole band structures calculated for Ge/Si NWs. Results for pure Ge NWs are also presented for comparison. The additional shell of Si ( $t = 1 \text{ nm}$ ) in Ge/Si NWs has a strong influence on the bands. The heavy-hole bands are clearly pushed to lower energy with respect to the valence-band edge. Remarkably, this effect prevails in  $\langle 001 \rangle$ ,  $\langle 110 \rangle$ ,  $\langle 111 \rangle$ , and  $\langle 112 \rangle$  orientations.

In the situations shown in Fig. 1, holes in Ge/Si NWs mainly occupy light-hole bands, at least when the carrier concentration is not too high. As a consequence, the influence of the Si shell is considerable on the hole mobility (Fig. 2). Whatever the NW orientation, the mobility is much larger in Ge/Si NWs than in Ge NWs without Si shell. Even in  $\langle 001 \rangle$  NWs, where low mobilities are predicted in pure Ge NWs,<sup>18</sup> the effect of the shell is such that the mobilities

become larger than in bulk Ge for  $d > 6 \text{ nm}$ . Remarkably, in the 2–10 nm range where we are able to perform the calculations, the mobilities continuously increase with diameter, with almost no sign of saturation. Previous works on Si NWs<sup>13–16</sup> have shown that the mobility is influenced in a subtle manner by many scattering processes between different bands, explaining why its variation with size may not be perfectly monotonous, as shown, for example, in Fig. 2 by the small dip at  $d = 8 \text{ nm}$  for the  $\langle 110 \rangle$  orientation. This sensitivity is even larger here since the mobility is high and therefore scattering rates are small.

It was found in Refs. 18 and 25 that the mobility of stretched Si or Ge NWs basically depends on a single parameter,  $\varepsilon_{\parallel} - \varepsilon_{\perp}$ . As shown in Fig. 2, Ge/Si NWs indeed show similar mobilities as Ge NWs stretched to the same  $\varepsilon_{\parallel} - \varepsilon_{\perp}$ . We therefore conclude that the large enhancement of the mobility in Ge/Si NWs is entirely due to the strains induced by the shell.

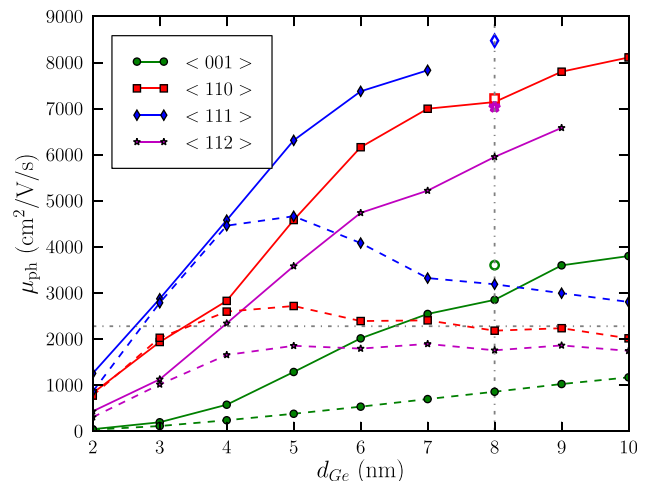


FIG. 2. Mobilities in unstrained pure Ge NWs (dashed lines) and Ge/Si core/shell NWs (solid lines) with  $\langle 001 \rangle$ ,  $\langle 110 \rangle$ ,  $\langle 111 \rangle$ , and  $\langle 112 \rangle$  orientations at  $T = 300 \text{ K}$ . The hollow markers at  $d = 8 \text{ nm}$  represent the mobilities in pure Ge NWs under the same strain ( $\varepsilon_{\parallel} - \varepsilon_{\perp}$ ) as in Ge/Si core/shell NWs.

The low mobilities predicted in the thinnest NWs (Fig. 2) are due to the strong enhancement of the electron-phonon coupling by the confinement.<sup>13–16</sup> However, with increasing diameter of the NWs, this is outbalanced by the effects of strains induced by the Si shell.

Our calculations show that mobilities up to 8000 cm<sup>2</sup>/V/s, and probably above for larger diameters, could be reached in Ge/Si NWs. As a result, very long mean free paths above 100 nm are predicted at 300 K (Fig. 3). Experimentally, room-temperature ballistic transport has been reported in Ge/Si FETs with a 170 nm long channel ( $d = 10$  nm).<sup>3</sup>

As expected, the phonon-limited mobility of holes in Ge/Si NWs strongly depends on the temperature (Fig. 4). It varies like  $T^{-2.4}$  at high  $T$  ( $T > 200$  K) when holes are scattered by both acoustic and optical phonons, and approximately like  $T^{-1}$  at lower  $T$  when only acoustic phonons are involved. A similar temperature behavior is found in bulk Ge.<sup>27</sup> In average, the mobility increases by factor  $\sim 14$  when  $T$  is reduced from 300 K to 100 K. For comparison, the mobility measured in Ge/Si<sub>0.7</sub>Ge<sub>0.3</sub> NW FETs varies only by a factor  $\sim 2$  in the same range of temperature,<sup>6</sup> while in bulk Ge it varies by a factor  $\sim 13$ .<sup>27</sup>

In order to study the influence of the carrier density on the mobility, we have also performed self-consistent Schrödinger-Poisson calculations. We have considered a gate-all-around geometry with a 1-nm-thick HfO<sub>2</sub> gate oxide. Self-consistency can have significant effects on the charge distribution and band structure, with a continuous transition from bulk toward interface accumulation at large concentration. For  $d = 6$  nm and  $t = 1$  nm, the hole mobilities significantly decrease for carrier densities above  $1 \times 10^6$  cm<sup>-3</sup> (or  $3 \times 10^{18}$  cm<sup>-3</sup>) (Fig. 5). Indeed, the average carrier velocity goes down as the lower-lying heavy-hole bands get populated, and scattering is strengthened since there are many more allowed transitions.<sup>16</sup>

Even if experiments are usually performed on somehow thicker NWs ( $d > 10$  nm),<sup>4–6,8–10</sup> the large gap between measured and calculated mobilities (more than a factor 10) suggests that extrinsic scattering mechanisms limit the hole transport in Ge/Si core/shell NWs, even at

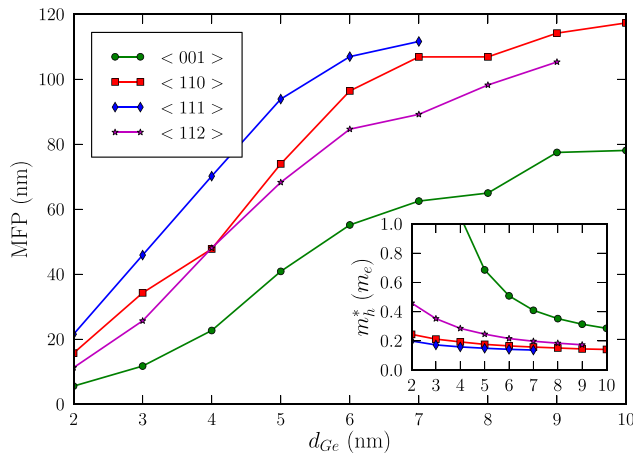


FIG. 3. Mean free paths corresponding to the phonon limited mobilities in Ge/Si core/shell NWs at 300 K. The mean free path is defined as  $\frac{\mu_{ph}}{e} \sqrt{k_B T m_h^*}$ , where  $m_h^*$  is the carrier effective mass at the top of valance band and is shown in the inset.

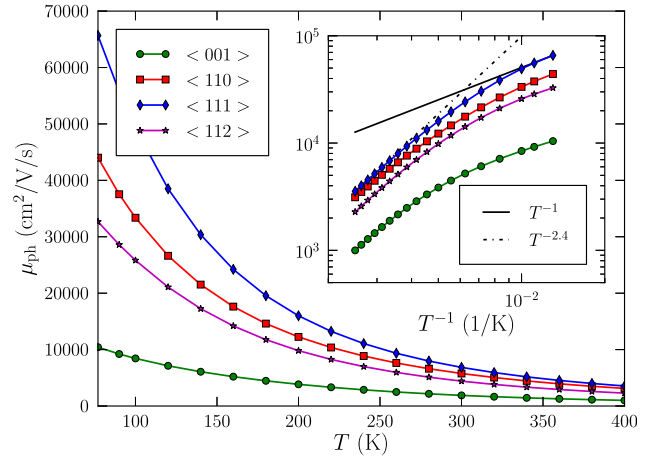


FIG. 4. Temperature dependence of the low field mobility in Ge/Si core/shell NWs (core diameter = 6 nm, shell thickness = 1 nm).

room temperature. The experimental dependence of the mobility on temperature,<sup>6</sup> which is much weaker than our predictions and than in bulk, also supports this conclusion. Since the NWs are not intentionally doped, the most probable extrinsic mechanisms are growth impurities and defects, remote Coulomb, and interface roughness scattering. This last mechanism is usually dominant at high carrier density—yet it was recently ruled out because the mobility measured on Si/Ge FETs was found independent on the diameter in the 15–30 nm range.<sup>9</sup> However, such a diameter-independent mobility likely results from the localization of holes at the Si/Ge interface in the strong inversion regime, which makes the hole gas more “2D” than “1D”-like at high densities in this range of diameters. Therefore, the observed independence of the mobility on the diameter does not necessarily mean that interface roughness scattering is not present.

It is interesting to compare the situation in Ge/Si NWs with the well-known case of GaAs/AlGaAs heterostructures.<sup>28,29</sup> After many years of efforts, it has been possible to grow remotely doped high quality layers characterized by a high

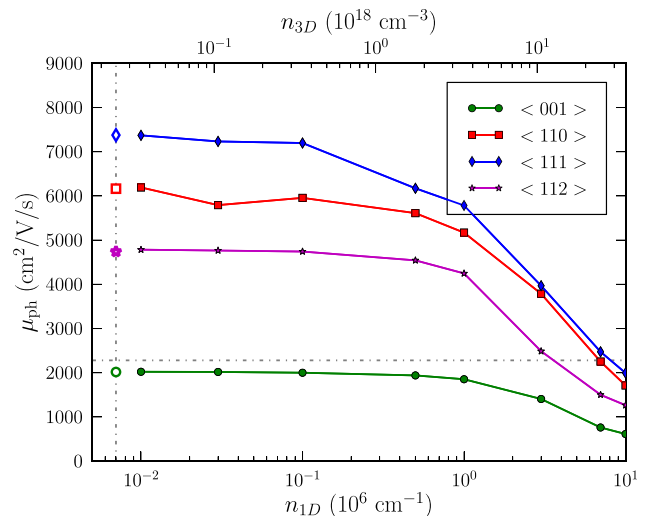


FIG. 5. Mobility versus carrier density in Ge/Si core/shell NWs (core diameter = 6 nm, shell thickness = 1 nm) at 300 K. The leftmost hollow markers are the low field (non self-consistent) mobilities.

mobility ( $\sim 7000 \text{ cm}^2/\text{V/s}$  at 300 K and  $> 10^6 \text{ cm}^2/\text{V/s}$  below 10 K). These figures are close to the inherent limits, i.e., the phonon-limited mobilities.<sup>28,29</sup> Therefore, we believe that there is considerable room for improvement in Ge/Si NWs. Obviously there are difficulties underlying the large lattice mismatch in the Ge/Si system. It is indeed hard to grow thick ( $> 3 \text{ nm}$ ) epitaxial Si shells, especially on a cylindrical NW surface; the lattice mismatch may also favor Ge/Si interface and Si surface roughness,<sup>30</sup> which should in turn induce fluctuations of strains in the Ge core.

In summary, we have demonstrated that a Si shell on a Ge NW not only confines the holes in the Ge core but also induces strains that considerably improve the hole mobility, whatever the NW orientation. Very high mobilities, up to  $8000 \text{ cm}^2/\text{V/s}$ , can be reached if interface-roughness, impurity and remote Coulomb scattering can be reduced. These results should strongly motivate research on the growth of Ge/Si core/shell NWs with better surface and interface quality.

This work was supported by the French National Research Agency (ANR) project “NOODLES” ANR-13-NANO-0009-02. Part of the calculations was run on the TGCC/Curie machine using allocations from GENCI and PRACE.

<sup>1</sup>C. M. Lieber, *MRS Bull.* **28**, 486 (2003).

<sup>2</sup>C. Thelander, P. Agarwal, S. Brongersma, J. Eymery, L. Feiner, A. Forchel, M. Scheffler, W. Riess, B. Ohlsson, U. Gösele, and L. Samuelson, *Mater. Today* **9**, 28 (2006).

<sup>3</sup>W. Lu, J. Xiang, B. P. Timko, Y. Wu, and C. M. Lieber, *Proc. Natl. Acad. Sci. U.S.A.* **102**, 10046 (2005).

<sup>4</sup>J. Xiang, W. Lu, Y. Hu, Y. Wu, H. Yan, and C. M. Lieber, *Nature* **441**, 489 (2006).

<sup>5</sup>S. A. Dayeh, A. V. Gin, and S. T. Picraux, *Appl. Phys. Lett.* **98**, 163112 (2011).

<sup>6</sup>J. Nah, D. C. Dillen, K. M. Varahramyan, S. K. Banerjee, and E. Tutuc, *Nano Lett.* **12**, 108 (2012).

<sup>7</sup>M. Amato, M. Palumbo, R. Rurali, and S. Ossicini, *Chem. Rev.* **114**, 1371 (2014).

<sup>8</sup>D. C. Dillen, K. Kim, E.-S. Liu, and E. Tutuc, *Nat. Nanotechnol.* **9**, 116 (2014).

<sup>9</sup>B.-M. Nguyen, Y. Taur, S. T. Picraux, and S. A. Dayeh, *Nano Lett.* **14**, 585 (2014).

<sup>10</sup>A. P. Higginbotham, T. W. Larsen, J. Yao, H. Yan, C. M. Lieber, C. M. Marcus, and F. Kueemeth, *Nano Lett.* **14**, 3582 (2014).

<sup>11</sup>Y. Hu, J. Xiang, G. Liang, H. Yan, and C. M. Lieber, *Nano Lett.* **8**, 925 (2008).

<sup>12</sup>M. B. Prince, *Phys. Rev.* **92**, 681 (1953).

<sup>13</sup>W. Zhang, C. Delerue, Y.-M. Niquet, G. Allan, and E. Wang, *Phys. Rev. B* **82**, 115319 (2010).

<sup>14</sup>M. Luisier, *Appl. Phys. Lett.* **98**, 032111 (2011).

<sup>15</sup>N. Neophytou and H. Kosina, *Phys. Rev. B* **84**, 085313 (2011).

<sup>16</sup>Y.-M. Niquet, C. Delerue, D. Rideau, and B. Videau, *IEEE Trans. Electron Devices* **59**, 1480 (2012).

<sup>17</sup>H. Xu, X. Liu, G. Du, Y. Zhao, Y. He, C. Fan, R. Han, and J. Kang, *Jpn. J. Appl. Phys., Part 1* **49**, 04DN01 (2010).

<sup>18</sup>Y.-M. Niquet and C. Delerue, *J. Appl. Phys.* **112**, 084301 (2012).

<sup>19</sup>M. V. Fischetti and S. E. Laux, *J. Appl. Phys.* **80**, 2234 (1996).

<sup>20</sup>G. Liang, J. Xiang, N. Kharche, G. Klimeck, C. M. Lieber, and M. Lundstrom, *Nano Lett.* **7**, 642 (2007).

<sup>21</sup>Y. M. Niquet, D. Rideau, C. Tavernier, H. Jaouen, and X. Blase, *Phys. Rev. B* **79**, 245201 (2009).

<sup>22</sup>R. Tubino, L. Piseri, and G. Zerbi, *J. Chem. Phys.* **56**, 1022 (1972).

<sup>23</sup>D. M. Brown and R. Bray, *Phys. Rev.* **127**, 1593 (1962).

<sup>24</sup>D. Vanderbilt, S. H. Taole, and S. Narasimhan, *Phys. Rev. B* **40**, 5657 (1989).

<sup>25</sup>Y.-M. Niquet, C. Delerue, and C. Krzeminski, *Nano Lett.* **12**, 3545 (2012).

<sup>26</sup>C. Kloeffel, M. Trif, and D. Loss, *Phys. Rev. B* **90**, 115419 (2014).

<sup>27</sup>G. Ottaviani, C. Canali, F. Nava, and J. W. Mayer, *J. Appl. Phys.* **44**, 2917 (1973).

<sup>28</sup>G. Bastard, “Wave mechanics applied to semiconductor heterostructures,” in *Monographies de Physique* (Les Éditions de Physique, 1988).

<sup>29</sup>J. J. Harris, J. A. Pals, and R. Woltjer, *Rep. Prog. Phys.* **52**, 1217 (1989).

<sup>30</sup>Y. Y. Cao, G. Ouyang, C. X. Wang, and G. W. Yang, *Nano Lett.* **13**, 436 (2013).